



# Diamond Pixel Detector Systems in High Energy Physics

F. Hüggling for the RD42 collaboration

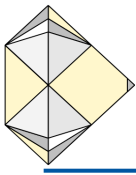


**PIXEL 2014**

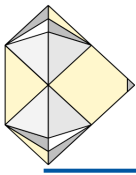
International Workshop on Semiconductor Pixel  
Detectors for Particles and Imaging

1 – 5 September 2014

Niagara Falls, Canada



- Why diamond?
  - diamond as sensor material
- Diamond pixel devices for HEP experiments
  - ATLAS Diamond Beam Monitor (DBM)
  - CMS Pixel Luminosity Telescope (PLT)
- Summary & Conclusions



# Diamond as sensor material

Property	Diamond	Silicon
Band gap [eV]	5.5	1.12
Breakdown field [V/cm]	$10^7$	$3 \times 10^5$
Intrinsic resistivity @ R.T. [ $\Omega$ cm]	$> 10^{11}$	$2.3 \times 10^5$
Intrinsic carrier density [ $\text{cm}^{-3}$ ]	$< 10^3$	$1.5 \times 10^{10}$
Electron mobility [ $\text{cm}^2/\text{Vs}$ ]	1900	1350
Hole mobility [ $\text{cm}^2/\text{Vs}$ ]	2300	480
Saturation velocity [cm/s]	$1.3(e)-1.7(h) \times 10^7$	$1.1(e)-0.8(h) \times 10^7$
Density [ $\text{g}/\text{cm}^3$ ]	3.52	2.33
Atomic number - Z	6	14
Dielectric constant - $\epsilon$	5.7	11.9
Displacement energy [eV/atom]	43	13-20
Thermal conductivity [W/m.K]	$\sim 2000$	150
Energy to create e-h pair [eV]	13	3.61
Radiation length [cm]	12.2	9.36
Spec. Ionization Loss [MeV/cm]	6.07	3.21
Aver. Signal Created / 100 $\mu\text{m}$ [ $e_0$ ]	3602	8892
Aver. Signal Created / 0.1 $X_0$ [ $e_0$ ]	4401	8323

★ Low leakage

★ Fast signal

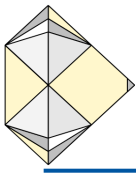
★ Low capacitance

★ Radiation hard

★ Heat spreader

★ Low signal

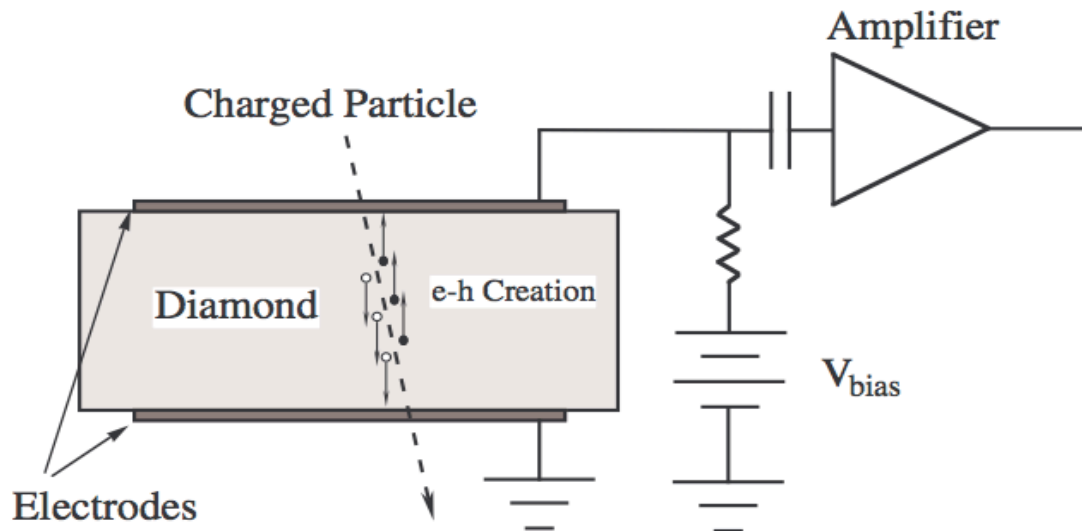
C. Bauer et al., Nucl. Instrum. Methods A 383, 64 (1996)  
 C. Manfredotti et al., Nucl. Instrum. Methods A 410, 96 (1998)  
 D. R. Kania et al., Diam. Relat. Mater. 2, 1012 (1993)



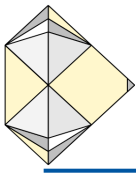
- External bias field across detector - connection to amplifier
- Charge trapping limits signal in pCVD -> aim for high fields
- Charge collection distance (*ccd*) used to characterize diamonds

$$Q_m = \frac{ccd}{t} Q_0$$

$$ccd = (\mu_e \tau_e + \mu_h \tau_h) E$$



- **GHz range current amplifiers** for beam monitoring/high rate
- **CSA (30ns to ~us shaping time)** for characterization, spectroscopy,
- **Strip/pixel FE ASICs** for trackers (~typically  $\tau \sim 10-20\text{ns}$ )



- Signal height decreases after irradiation due to trapping:
  - usually measured in degradation of the charge collection distance ccd with particle fluence  $\phi$
  - radiation induced traps decrease the mean free path  $\lambda$  according to

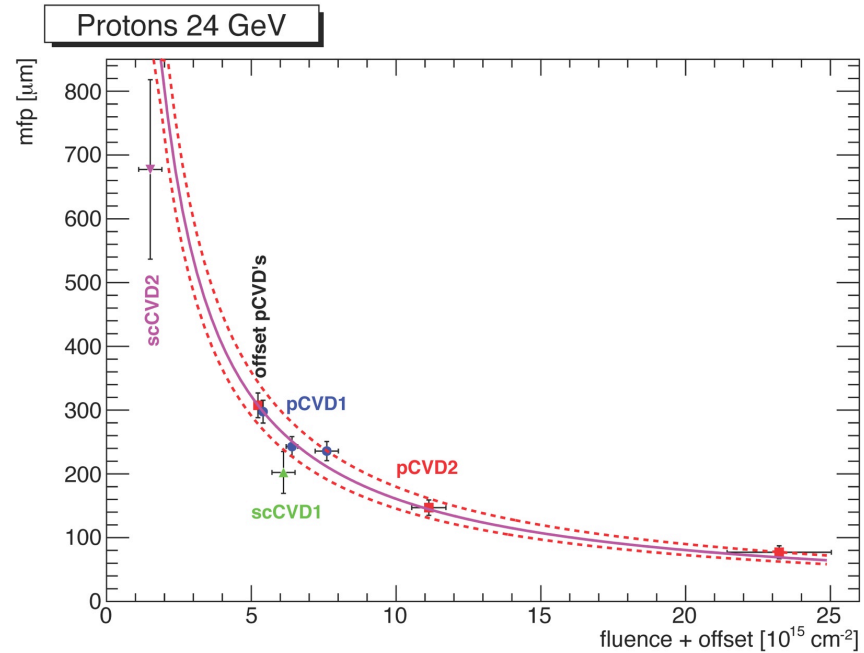
$$\frac{1}{\lambda} = \frac{1}{\lambda_0} + k\Phi$$

- Irradiation tests with protons and pions at different energies performed:

- pCVD diamonds up to  $1.8 \times 10^{16}$  p/cm<sup>2</sup>
- scCVD diamonds up to  $5 \times 10^{15}$  p/cm<sup>2</sup>

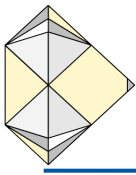
- Main results:

- pCVD material behaves like scCVD after  $\sim 5 \times 10^{15}$  p/cm<sup>2</sup> “pre-damage”
- pCVD and scCVD detectors follow same damage curve



$$k[24\text{GeV}p] \approx (0.62 \pm 0.07) \times 10^{-18} \mu\text{m}^{-1} \text{cm}^2$$

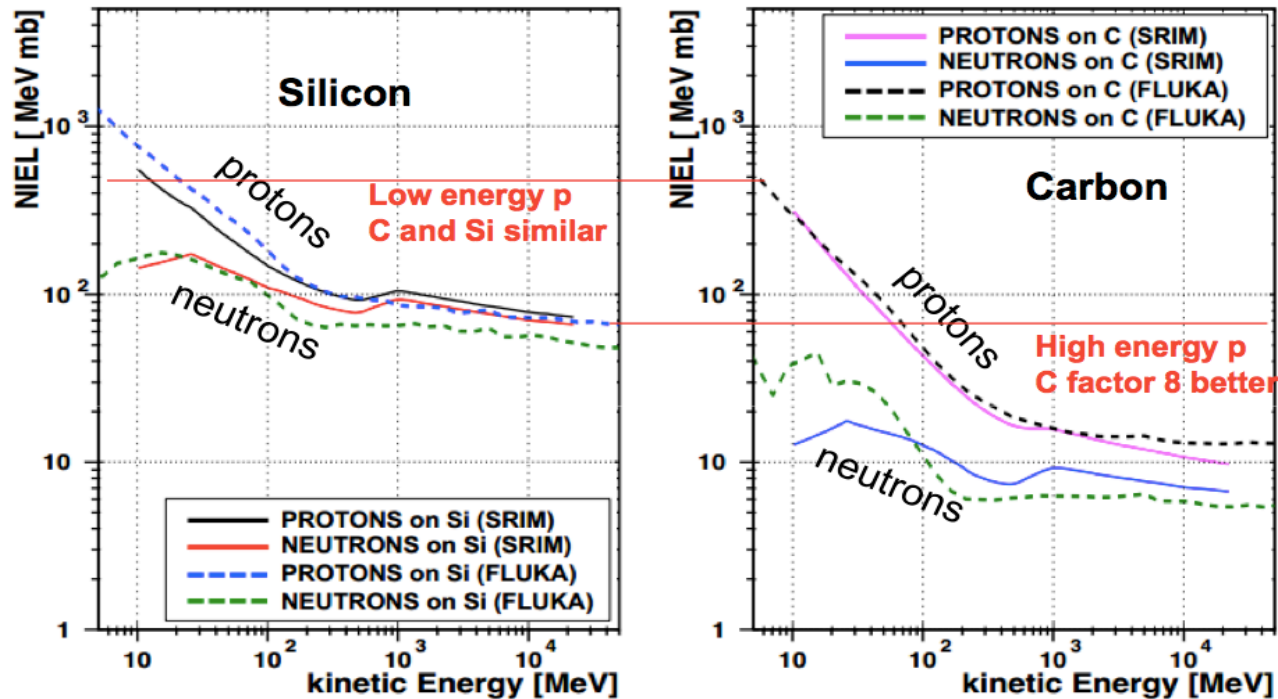
particle	energy/ momentum	relative k to 24 GeV p
p	24 GeV	1
p	800 MeV	1.7
p	70 MeV	2.7
p	25 MeV	4.2
$\pi$	300 MeV/c	2.9



## ... compared to simulations

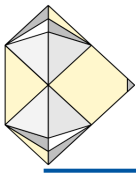
- NIEL calculations

- Good agreement down to 800 MeV, calculations predict stronger damage at lower energies than observed so far – under investigations with new irradiations
- Stronger damage in Si than C due to larger number of low-energy fragments

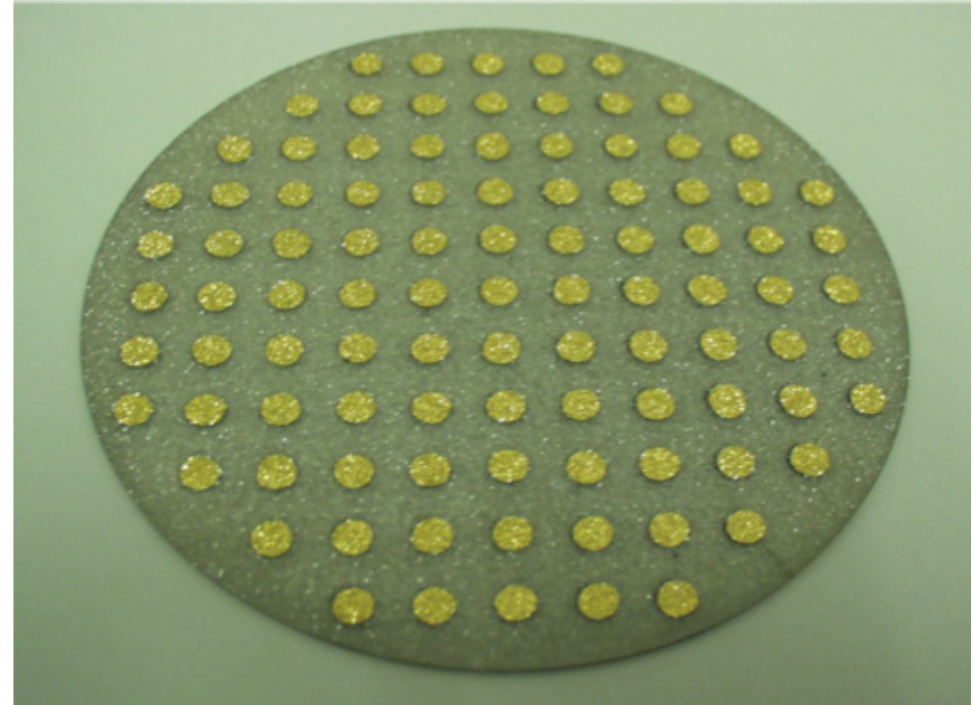


Moritz Guthoff, Wim de Boer, Steffen Müller, Simulation of beam induced lattice defects of diamond detectors using FLUKA, NIM 2014, [arXiv:1308.5419](https://arxiv.org/abs/1308.5419)

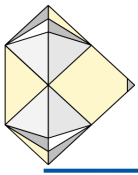
→ see next talk by Rainer Wallny for more details about radiation hardness



- Commercial applications require wafer scale growth
  - Heat sinks ( $>1200$  W/mK)
  - Electronics (power transistors)
  - IR windows, UV detectors (“visible blind”)...
- Well known only supplier so far was Element6/UK:
  - Detector-grade diamonds
  - Highest quality on 120mm wafers with CCD  $\sim 250$ - $300\mu\text{m}$
  - Up to 2mm thick for best quality

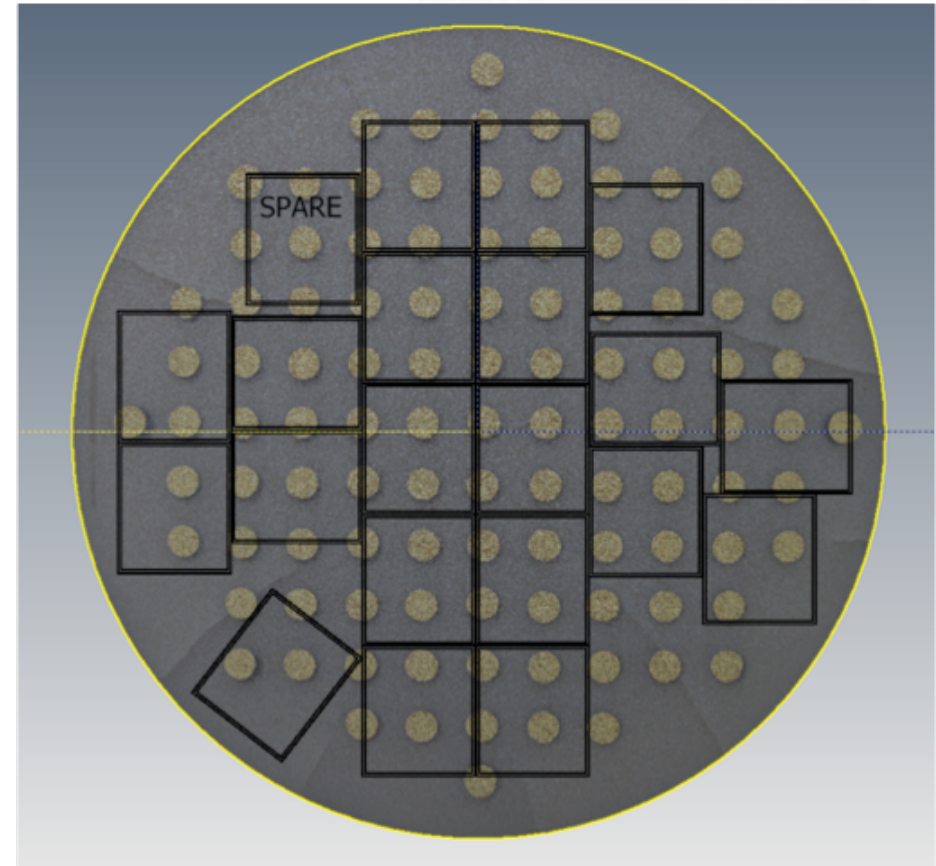
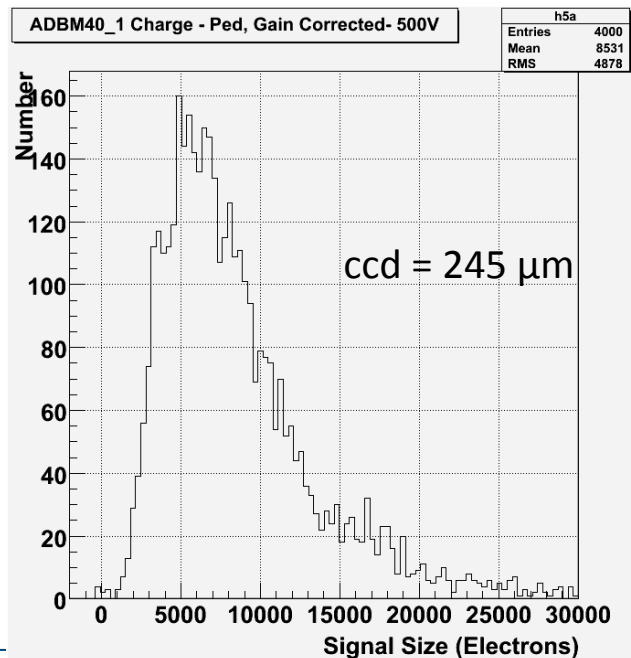


Courtesy Element6 / UK

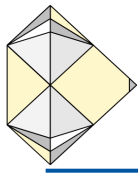


# New additional diamond supplier: II-VI

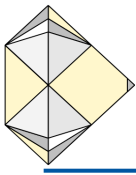
- All large samples in last year from II-VI
  - 26 ATLAS DBM sensors arrived during 2013
  - 10 CMS sensors were delivered in early 2014
- All have been (or soon will be) made into pixel detectors
- Overall quality is remarkable well



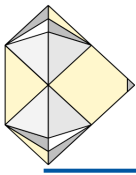




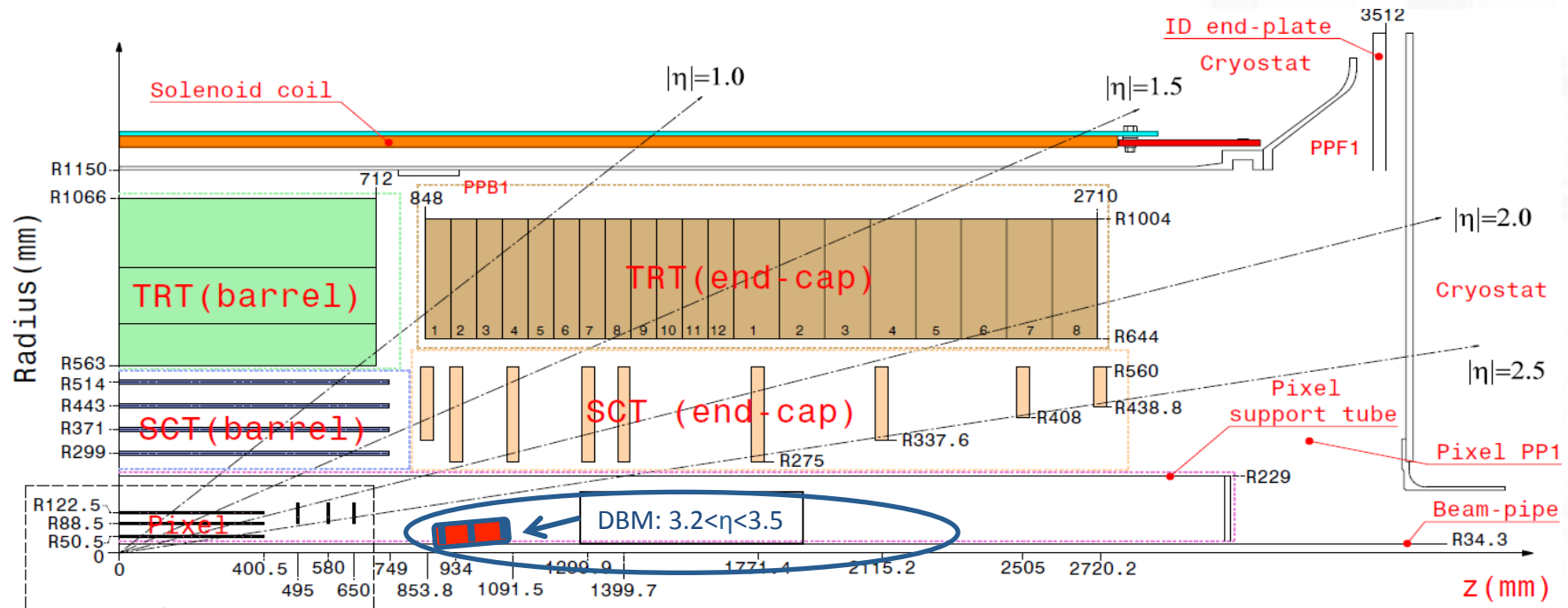
- Beam conditions monitors
  - Alice, ATLAS, CMS, LHCb
- LHC machine beam loss monitors (BLMs) → New for RD42
  - Operating in cryogenic conditions
- Current generation **Pixel Detectors**:
  - CMS PLT → see next talk by Rainer Wallny
  - **ATLAS DBM** → will focus on DBM in this talk
- Future LHC trackers
  - ATLAS, CMS, LHCb
  - 3D diamond devices

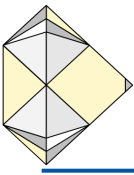


- Purpose
  - Bunch-by-bunch luminosity monitor (aim  $< 1\%$  per BC per LB)
    - Finer segmentation and larger acceptance than BCM
    - Never saturates
  - Bunch-by-bunch beam spot monitor
    - Need triple-module telescopes for (limited) tracking
    - Can distinguish collision tracks from beam halo
    - Unbiased sample, acceptance extends far along beam axis
- Design considerations
  - Baseline: four telescopes of 3 FE-I4 modules per side  $\rightarrow$  24 total
  - Avoid IBL insertion volume and ID acceptance ( $\eta > 2.5$ )
    - In front of BCM ( $\eta \sim 4.2$ ); partial overlap (cross-calibration)
  - Place in pixel support structure close to detector and beam pipe



- Part of pixel/nSQP volume, but uses IBL-services
  - e. g. 1000 V for detector bias
  - FE-I4 LV/power, readout/commands, temperature etc.
- nSQP re-assembly set original installation date to July 2013
  - Interleaved with nSQP panel re-installation → **October 2013**

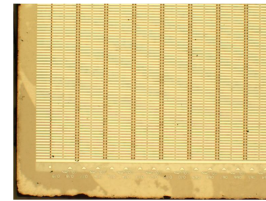




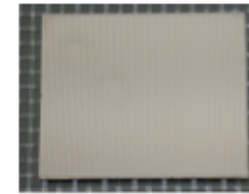
# Diamond pixel modules for ATLAS

## Completed Module

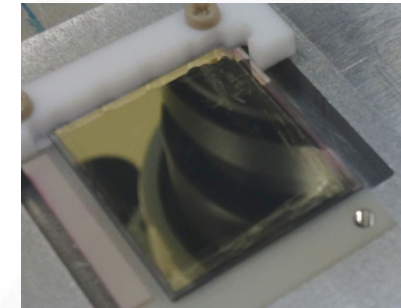
- Bump-bonding at IZM including pixel metallization
  - 21x18 mm<sup>2</sup> pCVD from DDL & II-VI
  - FE-I4 ATLAS IBL pixel chip
  - 336x80 = 26880 channels, 50x250 μm<sup>2</sup>
- Module assembly at CERN



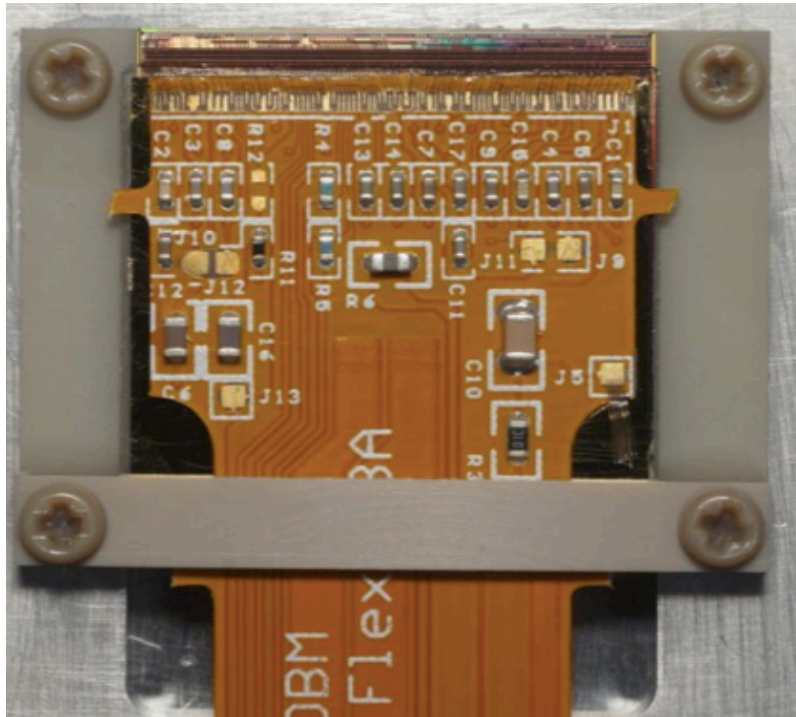
pCVD diamond with UBM



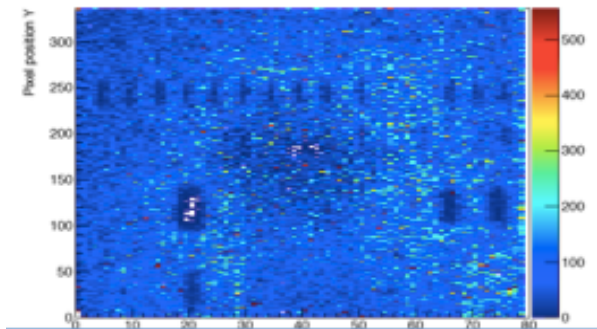
FEI4 chip



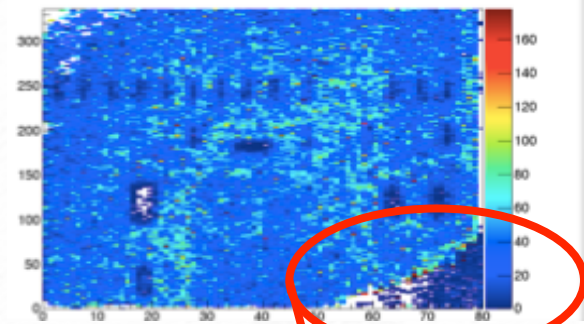
- Module QA
  - <sup>90</sup>Sr hitmaps



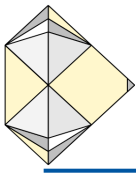
### MDBM17 (TDBM04)



### MDBM30 (not used)



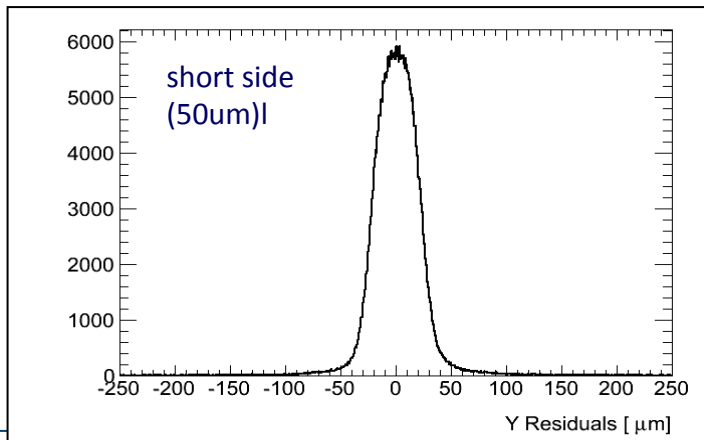
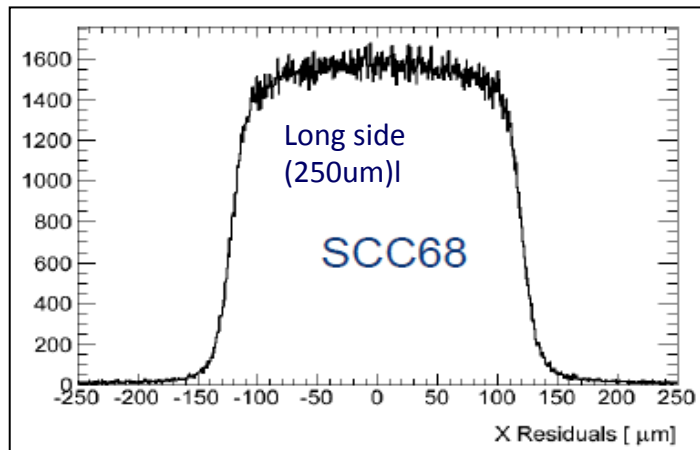
Example of disconnected corner



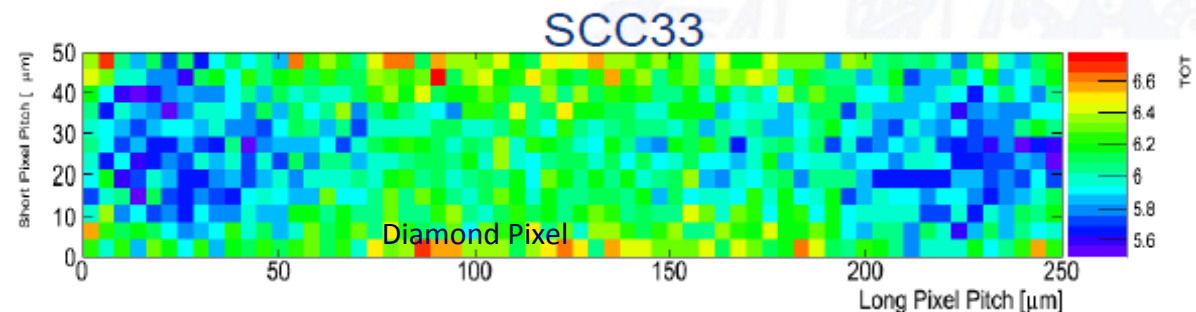
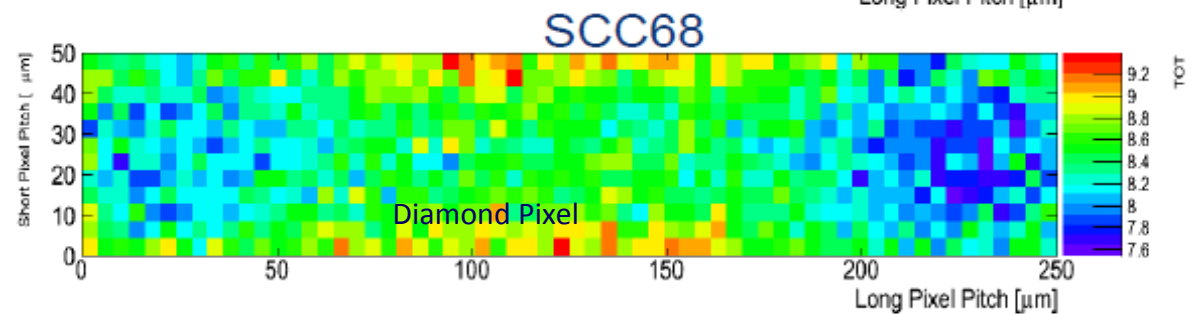
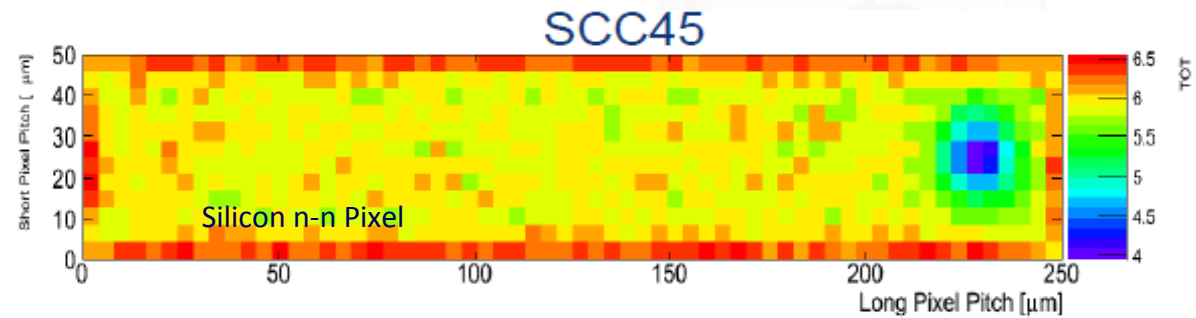
- Test beam results with FEI4+ diamond sensors in 2011 (CERN) and 2012 (DESY) showed good overall performance

## Time over threshold vs. hit position X/Y

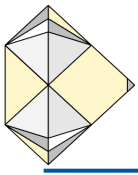
### Residual



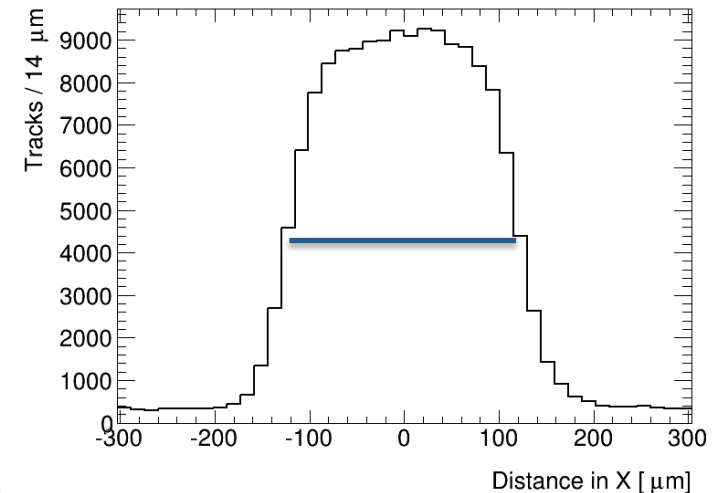
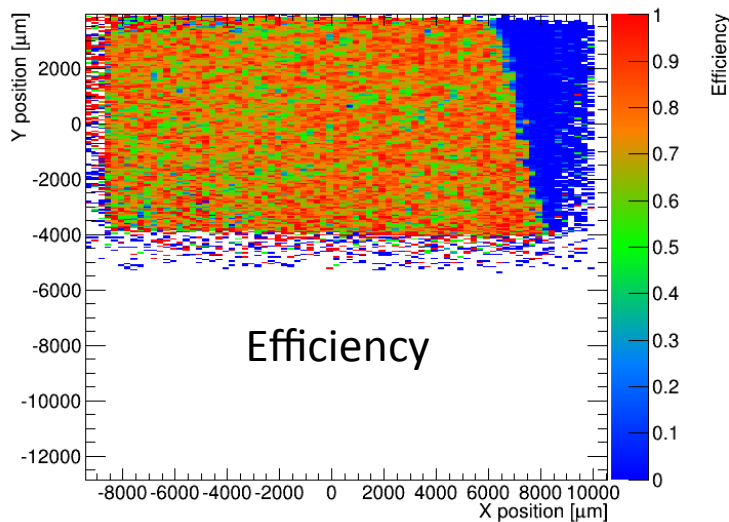
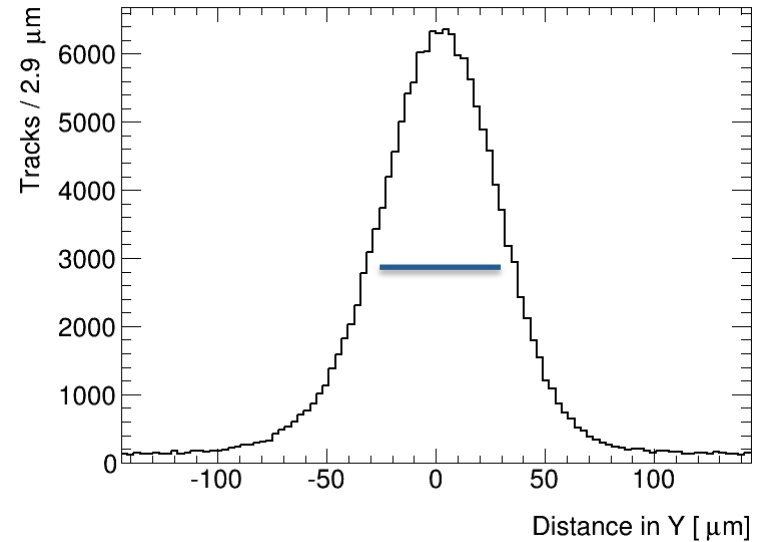
huegging@physik.uni-bonn.de



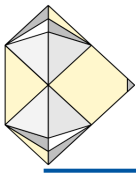
Pixel 2014, Niagara Falls - 02-Sept-2014



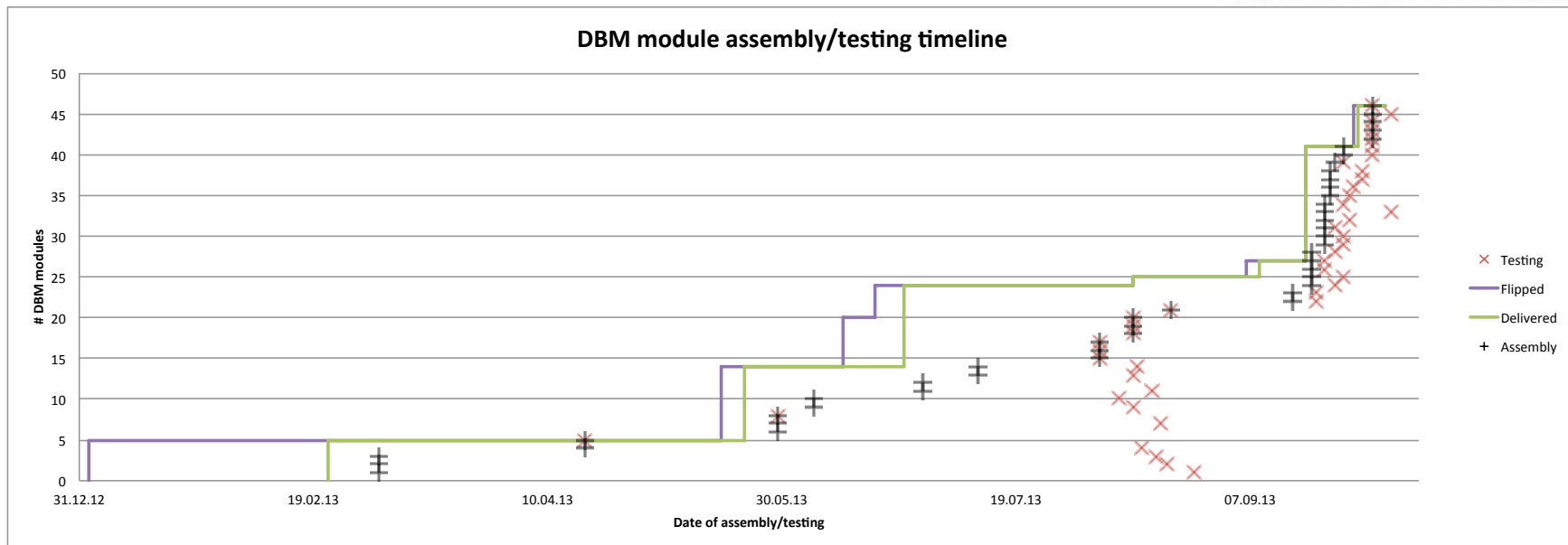
- MDBM-01 in 5 GeV electron beam at DESY
  - 1100 electron threshold but only 600V bias
  - Beam only populated top half of detector

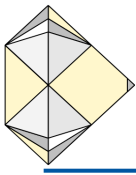


Hit residuals (pixel width)



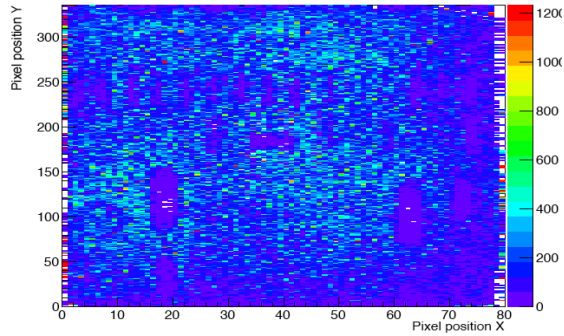
- Baseline: 24 modules to be installed
- Production model: Aim for 30 ATLAS-grade modules
  - Loss of 25 % during module assembly expected
    - Need parts to assemble 45 modules
      - 45 sensors, FE-I4's, flip-chippings, flexes etc.
      - 5 for irradiation studies
    - Plan on re-using diamond sensors as first modules assembled with FE-I4a, while FE-I4b final chip
      - In the end we re-worked 17 sensors
        - » This helped make up for flipping difficulties and shortage of sensors
- Reality shown to quite different → most used DBM modules were done within 4-6 weeks in late summer 2013 very close to the installation date
  - diamond supply to bump bonding was quite late → 9 DDL (E6), 15 II-VI. 10 refurbished DDL(E6) after re-trimming = 34 in total
  - flip chip difficulties during the production



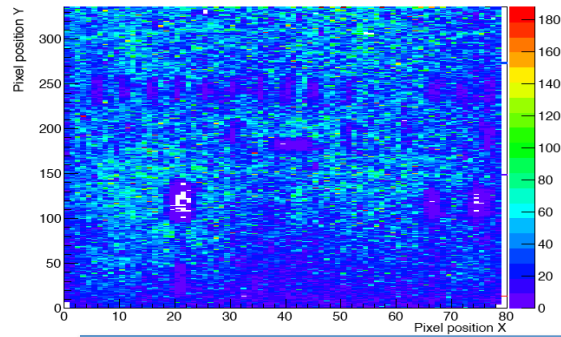


# Module bump connectivity

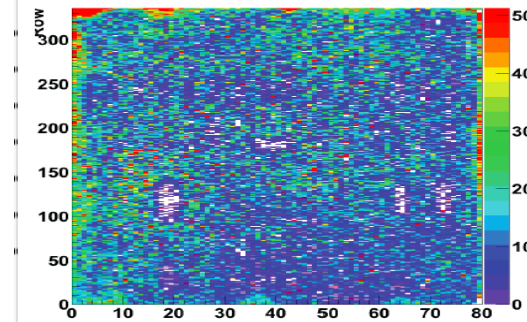
MDBM03 (TDBM01)



MDBM09 (TDBM01)

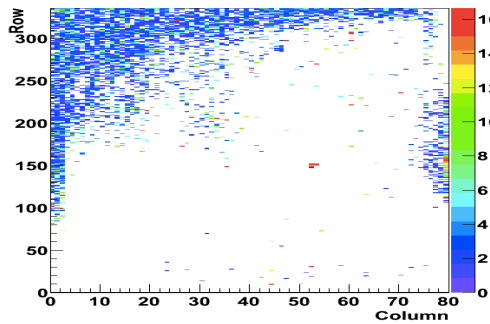


MDBM10 (re-worked)

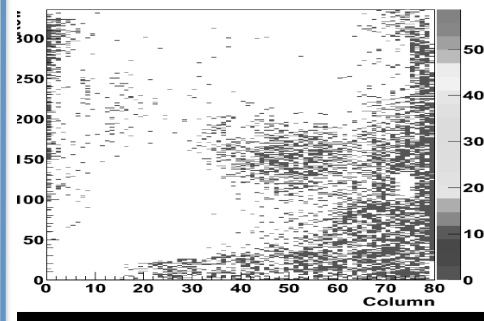


Bonded 1<sup>st</sup> batch with standard flip chip technique

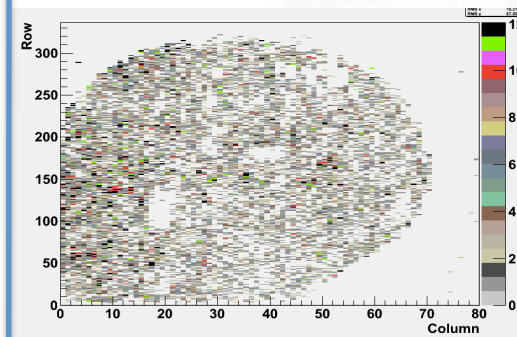
MDBM17 (reworked)



MDBM18 (reworked)

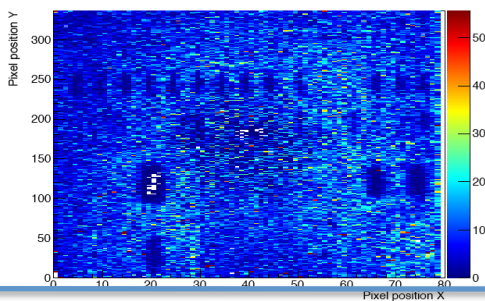


MDBM15 (15um bow)

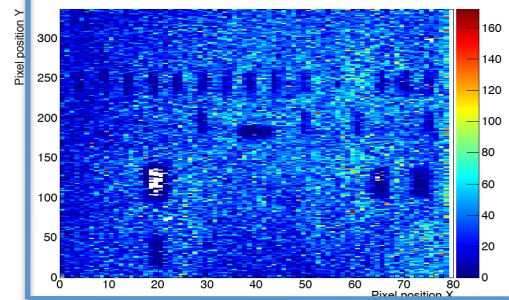


Bonded 2<sup>nd</sup> and 3<sup>rd</sup> batch with standard flip chip

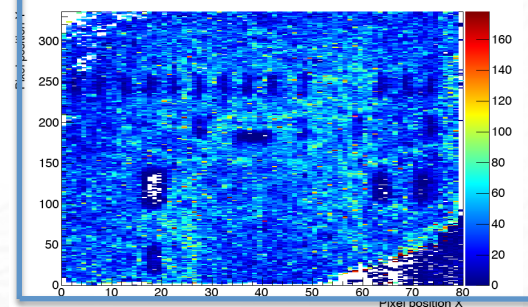
MDBM17 (not used)



MDBM31 (TDBM05)

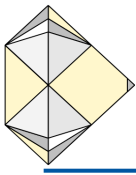


MDBM30 (not used)



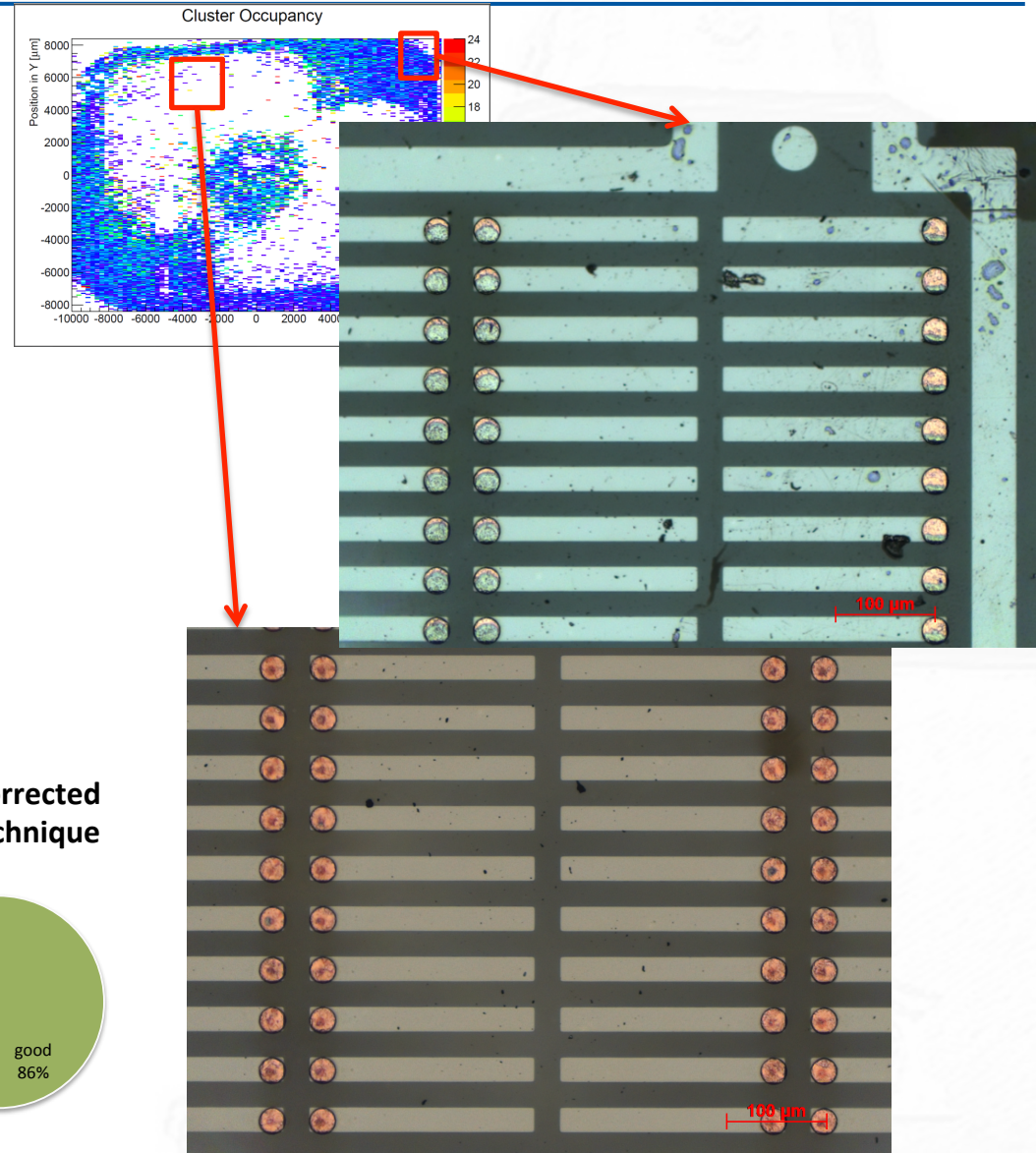
Bonded with new flip chip technique using a new bonder



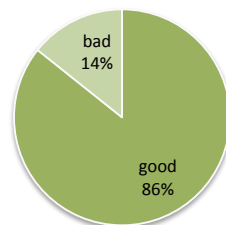
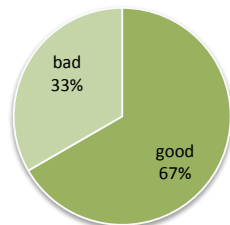
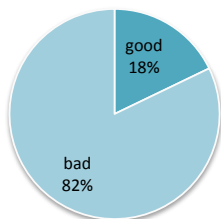
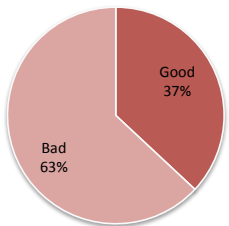


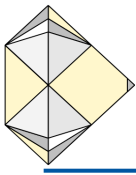
# Bump connectivity investigations & yields

- Open bumps are not soldered during reflow:
  - no solder attached to the Cu pads of the diamond
  - reason not fully understood
    - excluded bow of the sensor → only 2 diamonds showed significant bow
  - new flip chip technique applies pressure during the solder reflow process shows much better yield
- Yield estimations are difficult since many changes during the production
  - reworking of modules and diamonds
  - second reflow of assemblies with new technique
  - basically each assembly has its own history
  - 46 assemblies built and tested, 13 have been reworked or re-flipped
  - corrected yield excluded 4 assemblies with known issues: 2 with high bow and 2 have been undergo 2<sup>nd</sup> reflow with a mounted ceramic plate



Overall yield      yield standard technique      yield new technique      yield corrected new technique

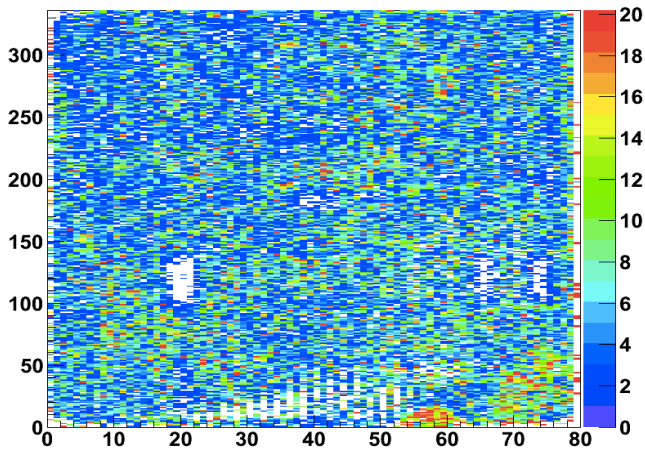




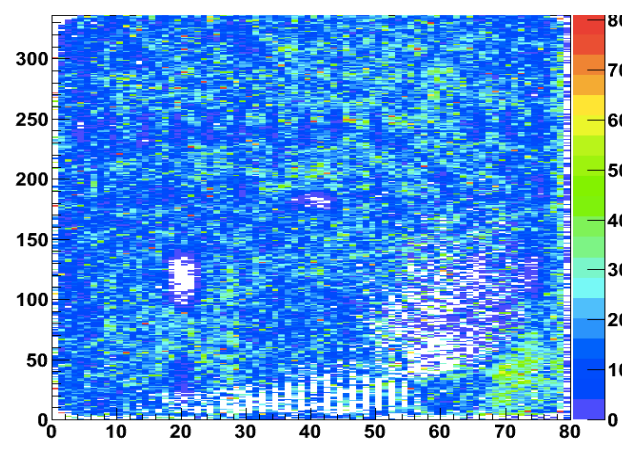
# Bump connectivity after thermal cycling

- QA included thermal cycling:
  - ~10 cycles from +40C to -20C
- Almost all modules showed no change in connectivity
- Only 3 modules were rejected → reason not clear, it is maybe connected to the initial bump connectivity problem

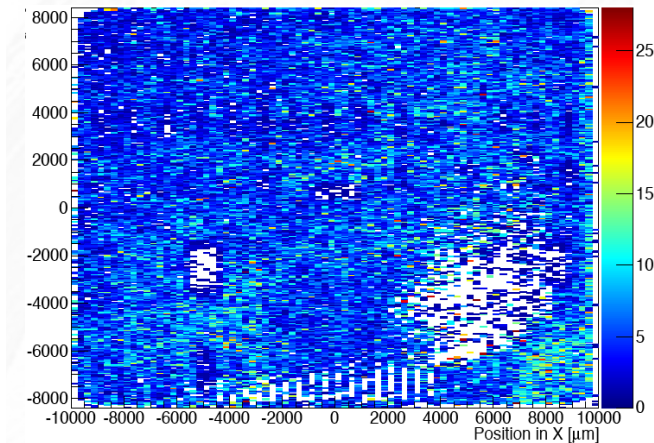
## MDBM-08



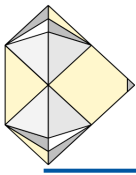
Before Thermal Cycling



After Thermal Cycling  
(once)



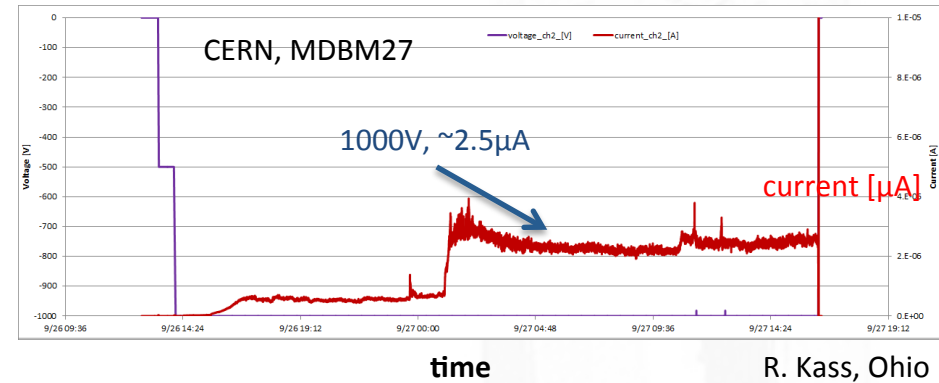
After Thermal Cycling  
(twice)



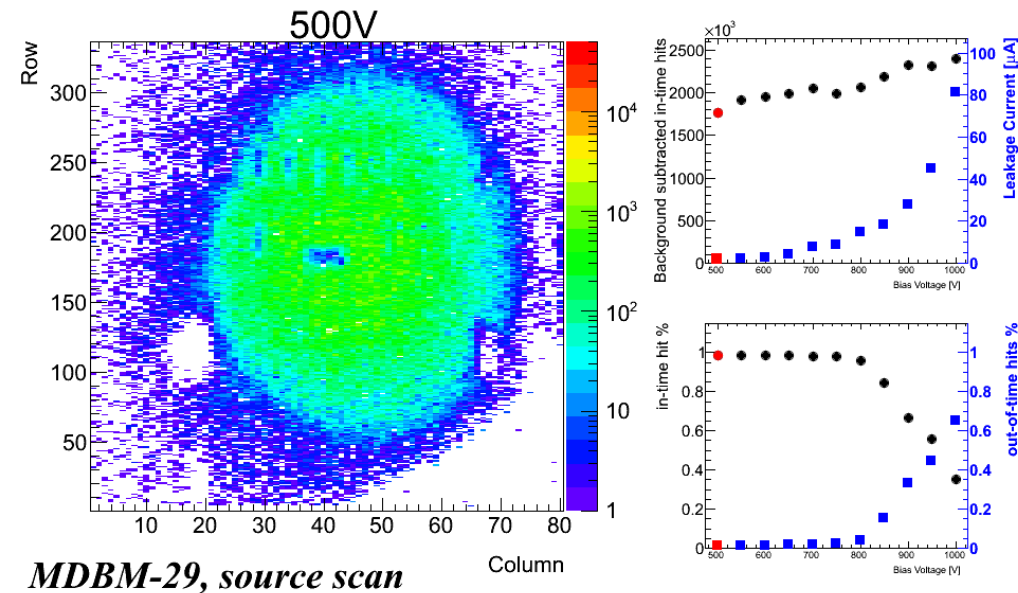
# HV stability and noise

- DBM module irradiated with  $^{90}\text{Sr}$  (1mC) at 1000V bias show unstable, rising leakage behavior with time
  - diamond prior to assembly fine and stable ( $>10\text{nA}@1\text{kV}$  for  $>1$  hr)
- $^{90}\text{Sr}$  source measurements at different bias voltages shows erratic noise behavior
  - noisy spots appear at higher voltages ( $\sim 850\text{V}$ ) and high currents ( $\sim 20\text{nA}$ )
  - these noisy spots are ‘unstable’ in time  $\rightarrow$  some spots not visible in other runs

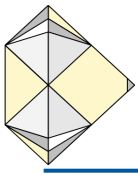
$\rightarrow$  limits the maximum operation bias of some DBM modules



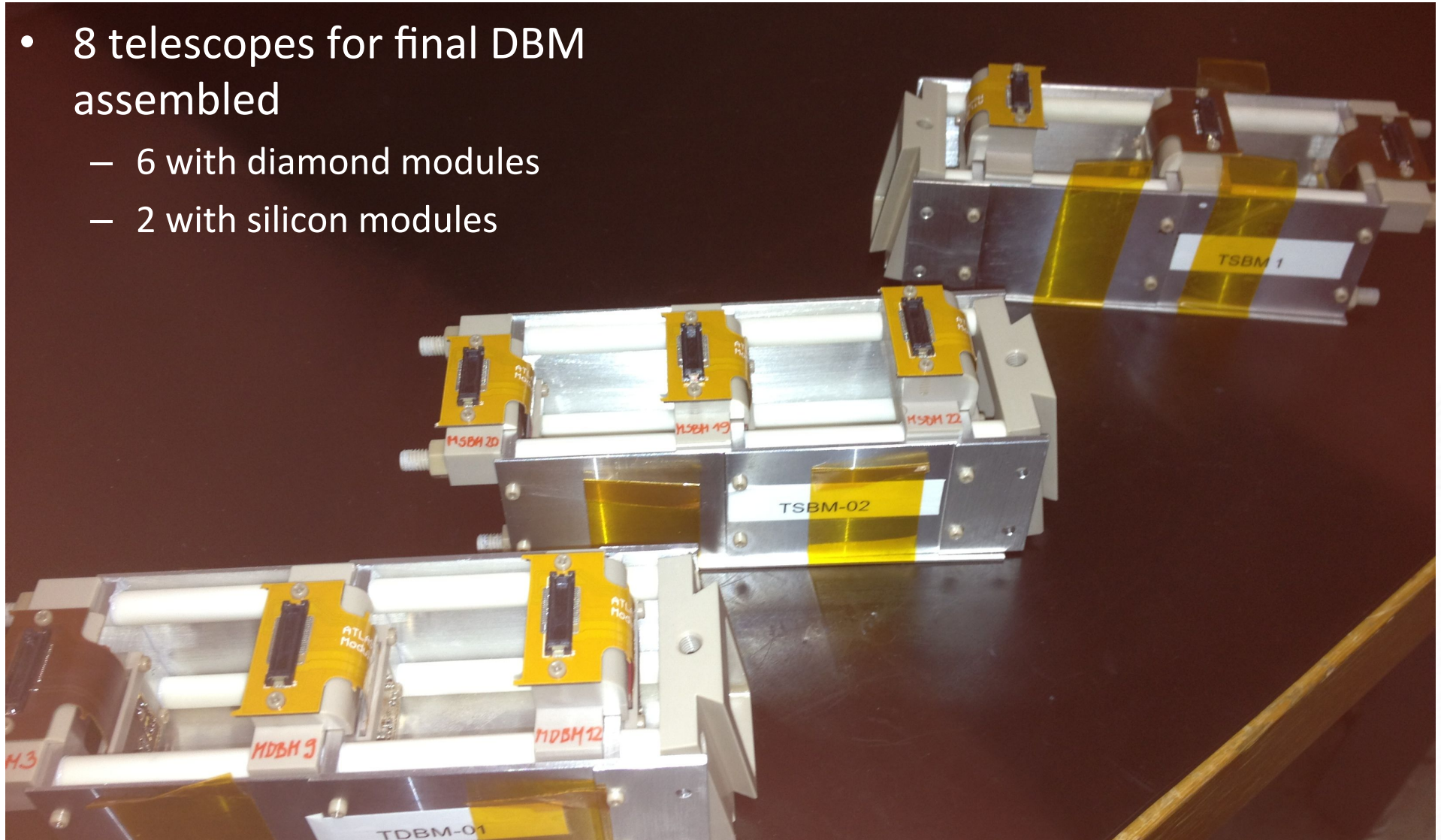
R. Kass, Ohio

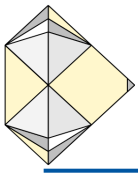


J. Moss, Ohio

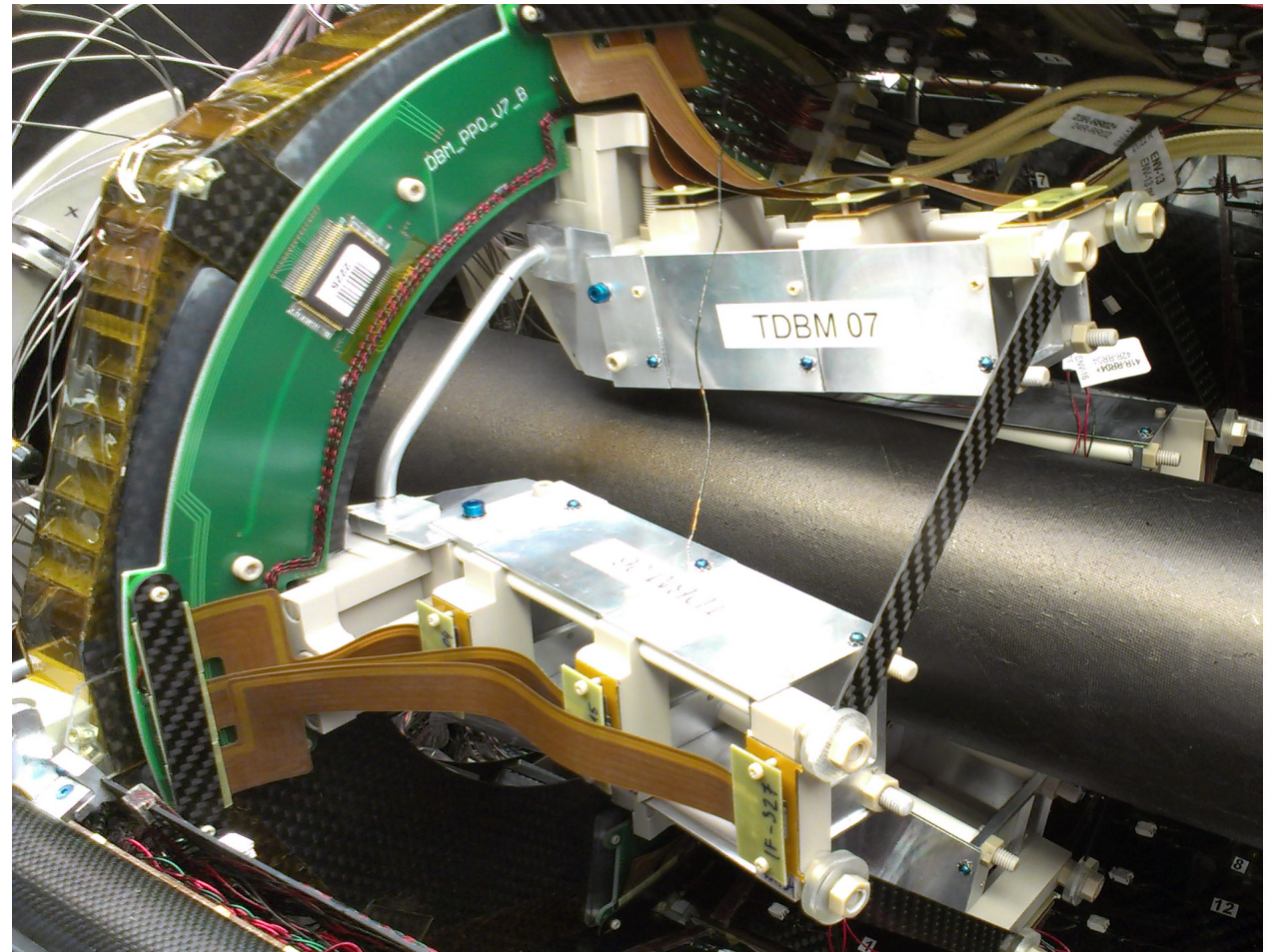
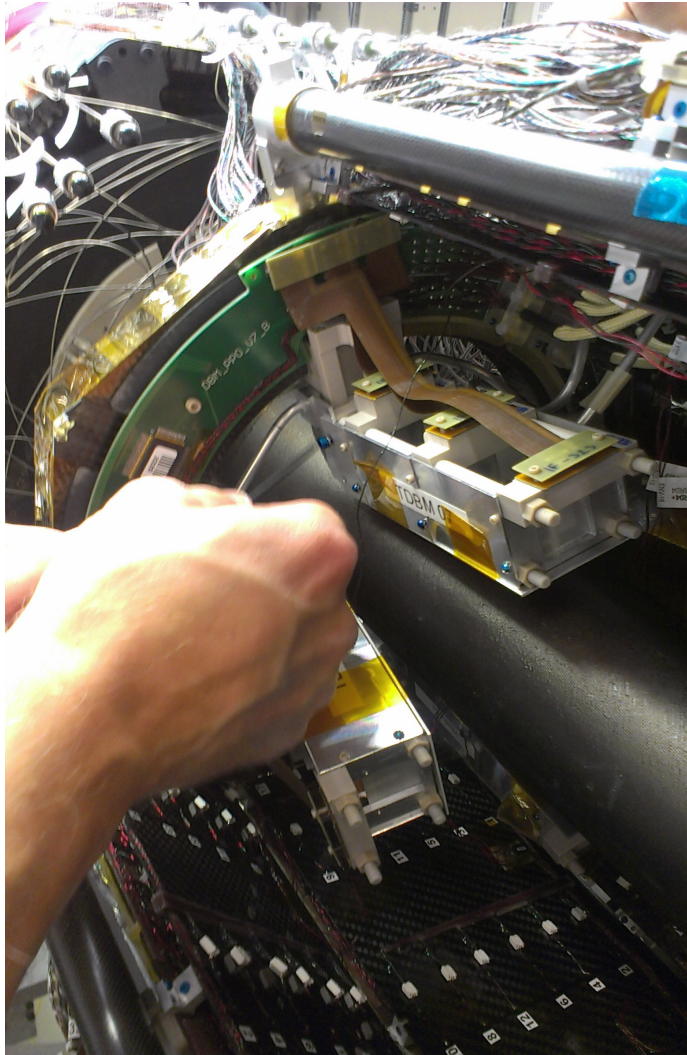


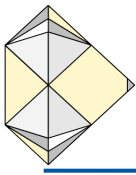
- 8 telescopes for final DBM assembled
  - 6 with diamond modules
  - 2 with silicon modules





# Telescope installation





# DBM commissioning

- DBM telescopes are fully integrated in the Pixel/IBL operation and readout → DBM is “15<sup>th</sup> IBL stave”
- Commissioning started in July 2014:
  - Connectivity of 24 DBM modules established and tested
  - Power (LV and HV) and temperature measurement tests
  - Readout tests with non final readout successfully tested for all modules
  - Readout tests with ROD/BOC system are currently ongoing

The screenshot displays the ATLPixIBLDBM control interface, which includes a 3D model of the detector assembly and several monitoring panels. The interface is divided into sections for Side A and Side C, each showing Hitbus1 and Hitbus2 voltage and current readings, Opto-board status, and WienerP4 PS settings for four modules (M1-M4).

**Side A Monitoring Data:**

Parameter	Value
Hitbus1 Voltage	1.476 V
Hitbus1 Curr	0.0882 mA
Hitbus2 Voltage	1.571 V
Hitbus2 Curr	0.0821 mA
Hitbus Voltage (HB_12)	1.500 V
Hitbus Voltage (HB_34)	1.500 V

**Side C Monitoring Data:**

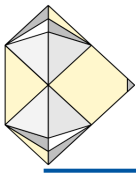
Parameter	Value
Hitbus1 Voltage	1.658 V
Hitbus1 Curr	0.0845 mA
Hitbus2 Voltage	1.633 V
Hitbus2 Curr	0.0745 mA
Hitbus Voltage (HB_12)	1.500 V
Hitbus Voltage (HB_34)	1.500 V

**WienerP4 PS Settings (Side A):**

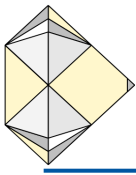
Module	VSet	VMeas	IMeas	Temp
M1	1.900	2.039	1.1554	25.2
M2	1.900	2.011	1.1945	21.7
M3	1.900	1.839	1.1643	25.9
M4	1.900	1.862	1.1530	24.8

**WienerP4 PS Settings (Side C):**

Module	VSet	VMeas	IMeas	Temp
M1	1.900	2.065	1.1765	29.1
M2	1.900	2.051	1.1875	28.1
M3	1.900	2.079	1.1939	27.1
M4	1.900	2.090	1.1963	29.2



- Diamond is an interesting but challenging sensor material for future HEP luminosity, beam monitor and tracking detectors in high radiation environment
- DBM production reveals several problems for large pixel devices
  - We learned a lot about bump bonding of large diamond pixel sensors
  - still try to understand all the problem and work with IZM on more robust and reliable procedure
  - noise hits and HV stability issues still under investigations
- ATLAS has installed the DBM inside the pixel package
  - Six high quality diamond telescopes and two silicon telescopes
  - Provide 100% acceptance for early DBM running
  - Commissioning close to finish
- Looking forward to operate DBM inside ATLAS during LHC Run 2



# RD-42 Collaboration

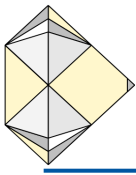
RD42 Collaboration 2014

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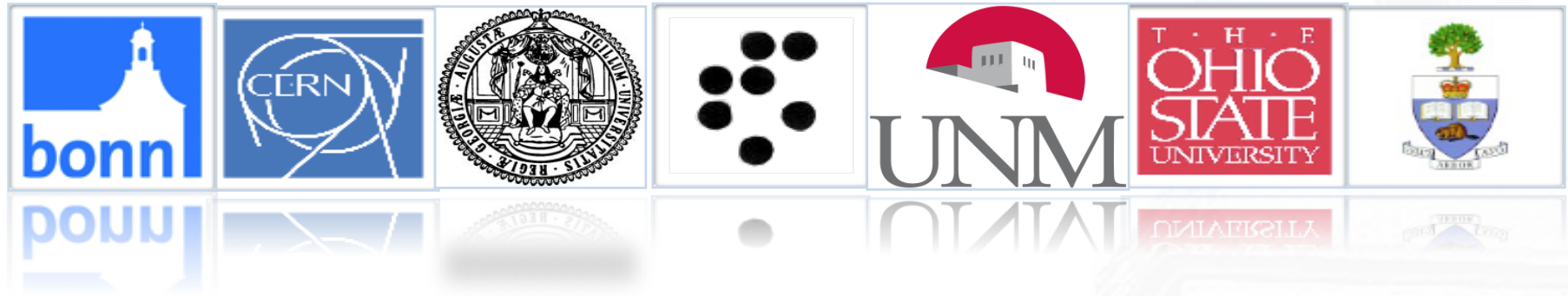
128 participants from 33 institutes





# Collaboration behind DBM

Bonn CERN Göttingen Ljubljana N.Mexico OhioSt Toronto



Students who built, debugged and commissioned the system:

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